

Evolution of Anisotropic Displacement Parameters and Superconductivity with Chemical Pressure in BiS₂-Based REO_{0.5}F_{0.5}BiS₂ (RE = La, Ce, Pr, and Nd)

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Abstract

In order to understand the mechanisms behind the emergence of superconductivity by the chemical pressure effect in REO_{0.5}F_{0.5}BiS₂ (RE = La, Ce, Pr, and Nd), where bulk superconductivity is induced by the substitutions with a smaller-radius RE, we performed synchrotron powder X-ray diffraction, and analyzed the crystal structure and anisotropic displacement parameters. With the decrease of the RE³⁺ ionic radius, the in-plane disorder of the S1 sites significantly decreased, very similar to the trend observed in the Se-substituted systems: LaO_{0.5}F_{0.5}BiS_{2-x}Se_x and Eu_{0.5}La_{0.5}FBiS_{2-x}Se_x. Therefore, the emergence of bulk superconductivity upon the suppression of the in-plane disorder at the chalcogen sites is a universal scenario for the BiCh₂-based superconductors. In addition, we indicated that the amplitude of vibration along the *c*-axis of the in-plane chalcogen sites may be related to the *T_c* in the BiCh₂-based superconductors.

BiS₂-based layered compounds have been extensively studied owing to the discovery of superconductivity in electron-doped phases and their relatively high transition temperatures (T_c), as high as 11 K [1–3]. A typical parent phase of the BiS₂-based superconductor is REOBiS₂ (RE: rare earth element), which has a layered structure composed of alternate stacks of REO insulating (blocking) layers and BiS₂ electrically conducting layers; it has a band gap of ~ 1 eV [2–5]. Electron carriers can be introduced in the BiS₂ layers by partial substitutions of the elements of the blocking REO layers [6–11]. For example, in LaO_{1-x}F_xBiS₂, the partial substitutions of O²⁻ sites with F⁻ generate electron carriers; the carrier concentration can be manipulated by varying the amount of substituted F [2]. Bulk superconductivity with a large shielding fraction in the magnetization measurements was not observed in electron-doped LaO_{1-x}F_xBiS₂ samples prepared using the solid-state reaction method at ambient pressure; however, filamentary superconducting states with a small shielding volume fraction were observed at $T_c \sim 2.5$ K [2]. In addition, the observed temperature dependence of the electrical resistivity was not metallic-like; it showed a weakly localized behavior in LaO_{1-x}F_xBiS₂, although band calculations suggested that the electron-doped LaO_{1-x}F_xBiS₂ should be metal [4, 5, 12]. These results suggested that the doped electrons were localized by the effect of structural disorder.

In order to induce bulk superconductivity in LaO_{1-x}F_xBiS₂, high pressure effects can be employed. The application of an external pressure induces bulk superconductivity with a T_c of ~ 10 K [13–15]. In addition, samples annealed under a high pressure (~ 2 GPa) also exhibit bulk superconductivity with a T_c of ~ 10 K [2, 16–18]. The emergence of bulk superconductivity and increase of T_c in the high-pressure phase can be attributed to the structural phase transition from the tetragonal low- T_c phase to the monoclinic high- T_c phase [13].

Another approach to induce bulk superconductivity in the LaO_{1-x}F_xBiS₂ system is to introduce a chemical pressure by an isovalent substitution, such as Ch (Ch: S, Se) and/or RE site substitutions. In LaO_{0.5}F_{0.5}BiS_{2-x}Se_x, the substitutions of Se for the S sites induces bulk superconductivity with a T_c of ~ 3.8 K [19, 20]. Another isovalent substitution is the RE site substitution. With the decrease of the RE³⁺ (mean) ionic radius in REO_{0.5}F_{0.5}BiS₂, the BiS₂ layer becomes compressed, in particular along the *ab*-plane direction, and bulk superconductivity is induced [21]. As the isovalent substitution does not significantly affect the carrier concentration, the structural optimization induces superconductivity in the Ch- and RE-substituted systems. In order to analyze the essential factor for the emergence of the superconductivity, we considered the commonality of the chemical pressure effects between the Ch- and RE substitutions, by introducing the concept of an in-plane chemical pressure [22].

The emergence of the bulk superconductivity in the LaO_{0.5}F_{0.5}BiS_{2-x}Se_x system was explained by the decrease in the in-plane disorder of the chalcogen sites with the increase of the Se content, which was detected through a crystal structure analysis of the synchrotron X-ray diffraction (SXR) pattern [23] and extended X-ray absorption fine structure (EXAFS) [24]. A similar relationship between the in-plane disorder and emergence of superconductivity was observed in Eu_{0.5}La_{0.5}FBiS_{2-x}Se_x [25–27].

For both systems, the Se substitutions induced a metallic electrical conductivity. Therefore, the in-plane disorder of the in-plane chalcogen sites is the factor that prevented the emergence of superconductivity and metallic conductivity in $\text{LaO}_{1-x}\text{F}_x\text{BiS}_2$. Therefore, we expect that a similar suppression of the in-plane disorder at the in-plane S sites (S1 site in Fig. 1(b)) can be attributed with the emergence of superconductivity in the RE-substituted systems. Neutron diffraction and pair distribution function analysis revealed the presence of the in-plane disorder and its relationship with the superconductivity, where RE is La or Nd [28, 29]. In addition, EXAFS measurements revealed a suppression of the Bi-S1-bond-disorder with the decrease of the RE^{3+} radius [30]. Therefore, in this study, we investigated the atomic displacement parameters of $\text{REO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ with RE = La, Ce, Pr, and Nd using SXRD and Rietveld refinement. Anisotropic analyses of the displacement parameters revealed that the in-plane displacement of S1 was very large for RE = La and gradually decreased with the decrease of the RE^{3+} ionic radius. This behavior is equal to that of the Se substitution. Therefore, the suppression of the in-plane disorder at the in-plane S1 (or Ch1) sites and emergence of superconductivity by the chemical pressure effects are universal for BiCh_2 -based superconductors. As unconventional superconductivity states are likely to appear in both Ch-substituted $\text{La}(\text{O},\text{F})\text{Bi}(\text{S},\text{Se})_2$ and RE-substituted $\text{REO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ systems [31–33], the universality revealed in this study could be employed to further understand the mechanisms of the superconductivity in the BiCh_2 -based superconductors.

Polycrystalline samples of $\text{REO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ with RE = La, Ce, Pr, and Nd were prepared using the solid-state-reaction method [2, 6–9]. A mixture of the starting materials was pressed into a pellet and annealed at 700 °C for 20 h in an evacuated quartz tube. SXRD was performed at the beamline BL02B2, SPring-8 at a wavelength of 0.49559 Å (proposal No.: 2017B1211). The SXRD experiments were performed with a sample rotator system at room temperature; the diffraction data were collected using a high-resolution one-dimensional semiconductor detector (multiple MYTHEN system [34]) with a step size of $2\theta = 0.006^\circ$. The crystal structure parameters were refined using the Rietveld method with the RIETAN-FP program [35]. Images with schematic models of the crystal structures were produced using VESTA [36].

Figure 1(a) shows the superconductivity phase diagram of $\text{REO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ as a function of the RE^{3+} ionic radius. The filamentary superconducting states observed for La are suppressed for Ce. A polycrystalline sample of $\text{CeO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ with 50% F substitution does not show superconductivity; however, $\text{CeO}_{0.3}\text{F}_{0.7}\text{BiS}_2$ with 70% F substitution shows bulk superconductivity upon the effect of high pressure [37]. As reported in Ref. 21, bulk superconductivity of $\text{REO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ appears at an RE^{3+} -radius of ~113 pm, which corresponds to RE = Pr or $\text{Ce}_{0.5}\text{Nd}_{0.5}$. T_c increases with the decrease of the RE^{3+} radius. The temperature dependences of the magnetization for the samples used in this study are

shown in Figure S1 of the Supplemental Material [38]. T_c values estimated from the magnetization measurements are represented with the larger circles in Fig. 1(a), which are in agreement with the results of a previous study [21].

Figure 2 shows the SXRD patterns and Rietveld refinement results for RE = (a) La, (b) Ce, (c) Pr, and (d) Nd. The Rietveld refinements were performed using a tetragonal $P4/nmm$ model. For RE = La, Ce, and Pr, a small portion (smaller than 4%) of RE_2F_3 impurity phases was detected, and a two-phase analysis was performed. For RE = Nd, unidentified impurity peaks were observed; hence, we analyzed the data for RE = Nd by a single-phase analysis. For all data, excellent fitting was also obtained at higher angles, required for a precise refinement of the displacement parameters.

Figures 3(a) and 3(b) show the dependences of the lattice constants a and c as a function of the RE^{3+} ionic radius. The lattice constant a linearly decreases with the decrease of the RE^{3+} radius. However, the lattice constant c does not exhibit a clear correlation with the RE^{3+} radius. Figure 3(c) shows the dependences of the Bi-S1 and Bi-S2 bond distances as a function of the RE^{3+} ionic radius (See Fig. 1(b) for the labeling of the S sites). It can be noticed that the in-plane Bi-S1 distance decreases with the decrease of the RE^{3+} radius, owing to the linear decrease in the lattice constant a . In contrast, Bi-S2 and interplane Bi-S1 distances do not decrease upon the introduction of chemical pressure, which may be related with the nonlinear change in the lattice constant c . However, as reported in Ref. 22, the essential factor for the emergence of superconductivity in the $REO_{0.5}F_{0.5}BiCh_2$ systems is the in-plane chemical pressure. In the considered $REO_{0.5}F_{0.5}BiS_2$ system, the amplitude of the in-plane chemical pressure is directly determined by the in-plane Bi-S1 distance. Therefore, we can analyze the relationship between the chemical pressure, superconductivity, and in-plane disorder using the considered samples.

We performed Rietveld refinements with anisotropic displacement parameters U_{11} and U_{33} for the in-plane Bi and S1 sites. Figure 4(c) illustrates U_{11} and U_{33} using a schematic model with RE = Pr. For the other sites, isotropic displacement parameters were assumed for the refinements. The obtained U_{11} and U_{33} for the Bi and S1 sites are plotted in Figs. 4(a) and 4(b), respectively. As expected, U_{11} for the S1 sites is very large for RE = La, and decreases with the decrease of the RE^{3+} radius, a very similar trend with that observed for U_{11} for the in-plane chalcogen sites in $LaO_{0.5}F_{0.5}BiS_{2-x}Se_x$ [23]. Therefore, the large suppression of the in-plane disorder at the in-plane chalcogen sites can be universally attributed with the emergence of bulk superconductivity in the $REO_{0.5}F_{0.5}BiCh_2$ systems. It is worth noting that U_{11} for the Bi sites slightly increases with the decrease of the RE^{3+} radius. Recently, Athauda et al. proposed that the increase in the in-plane displacement of Bi may be attributed with the superconductivity in $NdO_{1-x}F_xBiS_2$, while the in-plane displacement of S1 would induce carrier localization [29]. Our analysis also suggests that the increase of the in-plane displacement of the Bi sites may be related with the enhanced T_c for RE = Pr and Nd. Similar trend is observed for U_{33} in Fig. 4(b). Although U_{33} for the Bi sites does not considerably change with the decrease of the RE^{3+} radius,

U_{33} for the S1 sites dramatically changes with the replacement of the RE. It is worth noting that the evolution of U_{33} for the S1 sites seems to be linked with the enhancement of T_c . A similar evolution of the displacement ellipsoids is observed in Se-substituted $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiSSe}$, as shown in Fig. 5. Both RE and Ch substitutions suppress U_{11} for the Ch1 sites; however, they enhance U_{33} for the Ch1 sites. This trend may suggest that the amplitude of the one-dimensional large vibration of S1 is correlated with the T_c in this system. If this is valid, then the T_c increases when the phonon frequency decreases with the increase of the amplitude of the S1 vibration along the c -axis. This scenario is not consistent with the conventional phonon-mediated mechanisms. It is consistent with the isotope effect; no isotope effect was observed for the $\text{LaO}_{0.6}\text{F}_{0.4}\text{Bi}(\text{S},\text{Se})_2$ samples with ^{76}Se and ^{80}Se isotopes [31]. If such large vibrations of Ch1 are related with the enhancement of T_c , charge fluctuation should occur in the superconducting Bi-Ch1 plane. Then, the pairing phenomena mediated by charge fluctuations, proposed by theoretical and experimental studies [28, 29, 32, 39], may occur in the BiCh_2 -based system.

In conclusion, we investigated the crystal structure and anisotropic displacement parameters of $\text{REO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ with RE = La, Ce, Pr, and Nd, where bulk superconductivity is induced by substitutions with a smaller-radius RE, such as Pr or Nd. With the decrease of the RE^{3+} ionic radius, the lattice constant a and in-plane Bi-S1 distance monotonically decreased, which generated the in-plane chemical pressure effect. With the decrease of the RE^{3+} radius, the in-plane disorder of the S1 sites significantly decreased. This trend is very similar to those observed for Se-substituted $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiS}_{2-x}\text{Se}_x$ and $\text{Eu}_{0.5}\text{La}_{0.5}\text{FBiS}_{2-x}\text{Se}_x$. Therefore, the emergence of bulk superconductivity upon the suppression of the in-plane disorder at the Ch1 sites seems to be a universal scenario for the BiCh_2 -based superconductors. The analyses of the displacement parameters along the c -axis indicated that the amplitude of the one-dimensional vibration of S1 (or Ch1) along the c -axis was correlated with T_c in the BiCh_2 -based superconductors.

Acknowledgements

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- 38) [Supplemental Materials] Figure S1. Temperature dependences of the magnetization for $\text{REO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ (RE = (a) La, (b) Ce, (c) Pr, and (d) Nd).
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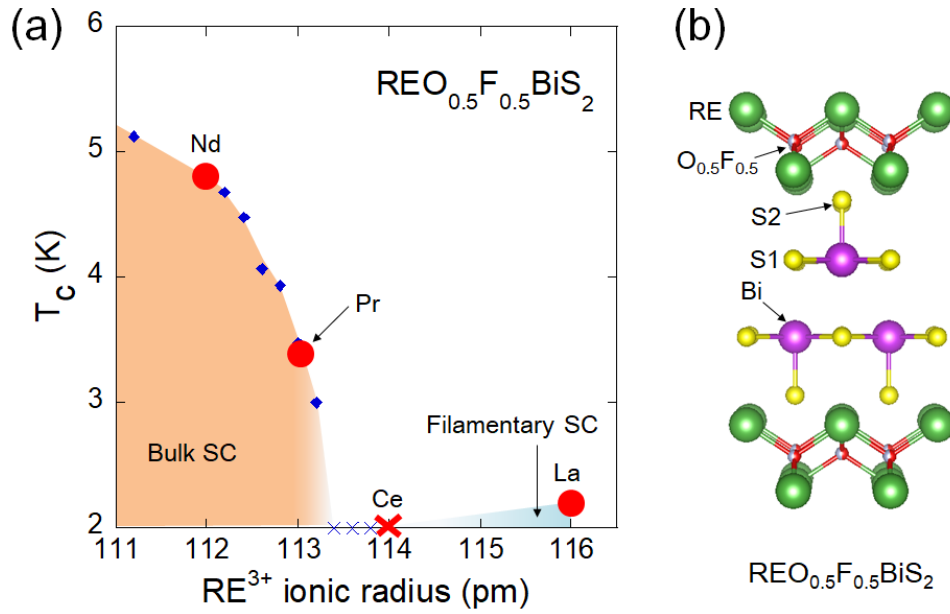


Fig. 1. (Color online) (a) Superconductivity phase diagram of $\text{REO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ as a function of the RE^{3+} ionic radius with a coordination number of 6. Data points for $\text{Ce}_{1-x}\text{Nd}_x\text{O}_{0.5}\text{F}_{0.5}\text{BiS}_2$ and $\text{Nd}_{1-x}\text{Sm}_x\text{O}_{0.5}\text{F}_{0.5}\text{BiS}_2$ have been published in Ref. 26. Bulk and filamentary SC denote the bulk and filamentary superconducting states with weak diamagnetic signals, respectively. (b) Schematic model of the crystal structure of $\text{REO}_{0.5}\text{F}_{0.5}\text{BiS}_2$.

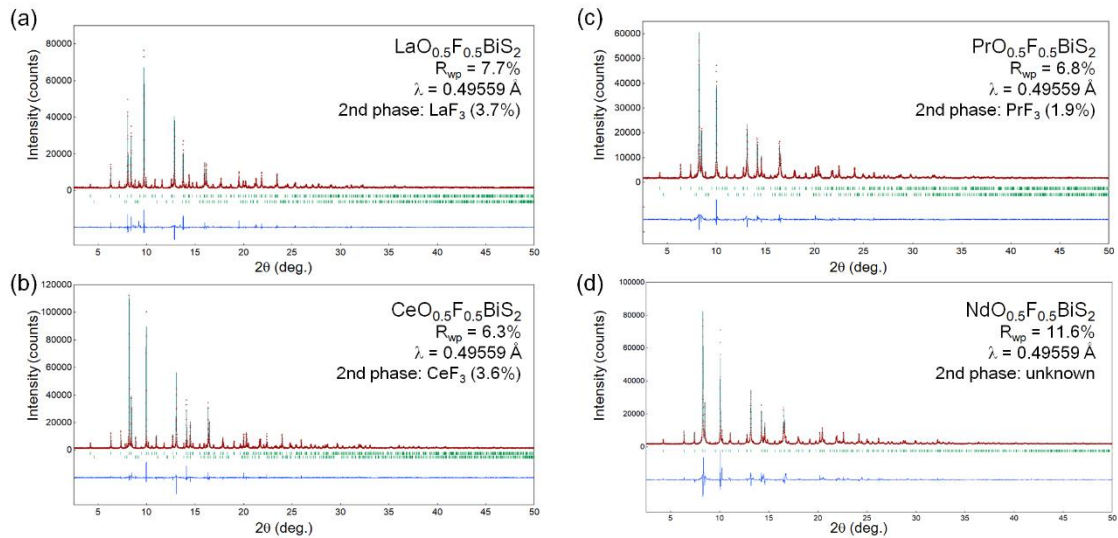


Fig. 2. (Color online) SXR D patterns for (a) $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, (b) $\text{CeO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, (c) $\text{PrO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, and (d) $\text{NdO}_{0.5}\text{F}_{0.5}\text{BiS}_2$.

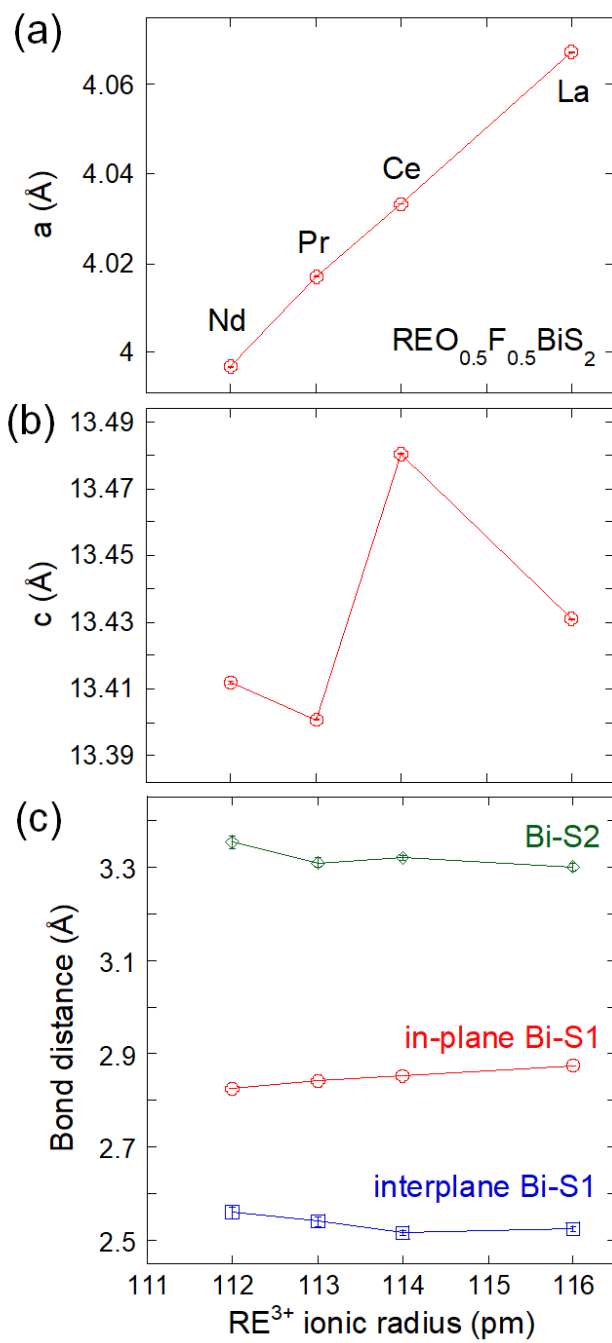


Fig. 3. (Color online) Dependences of the lattice constants (a) *a* and (b) *c*, and (c) Bi-S bond distances, as a function of the RE³⁺ ionic radius.

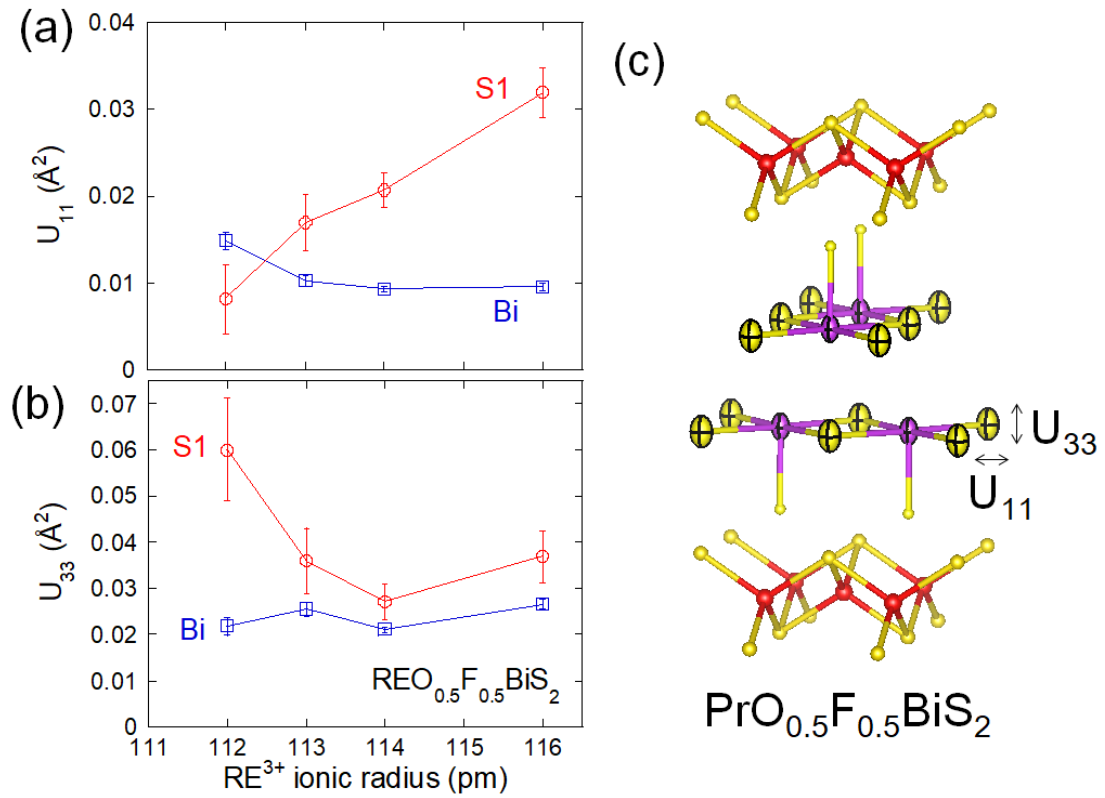


Fig. 4. (Color online) Dependences of the anisotropic displacement parameters (a) U_{11} and (b) U_{33} for the Bi and S1 sites as a function of the RE^{3+} ionic radius. (c) Schematic model of the crystal structure of $\text{PrO}_{0.5}\text{F}_{0.5}\text{BiS}_2$; 90%-probability displacement ellipsoids are outlined.

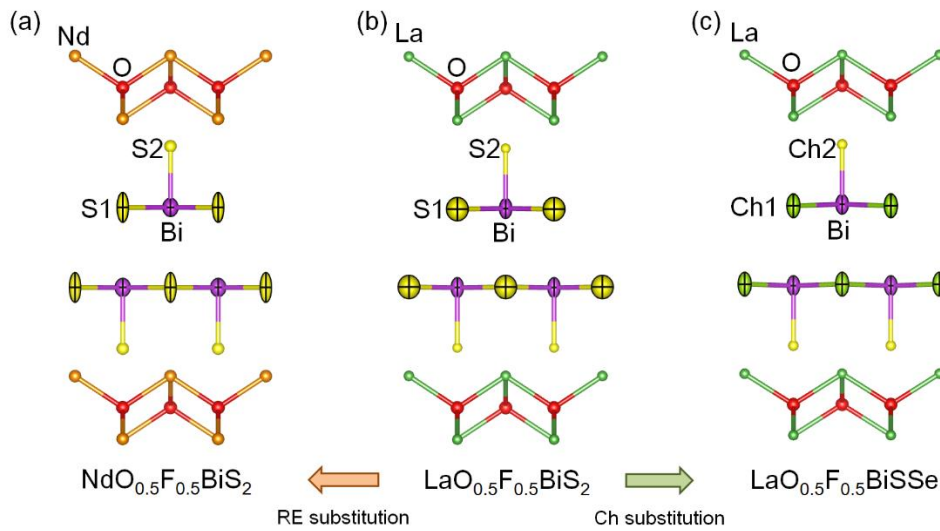


Fig. 5. (Color online) Evolution of the displacement ellipsoids (90% probability) by the effect of chemical pressure (RE or Ch substitutions) in the $\text{REO}_{0.5}\text{F}_{0.5}\text{BiCh}_2$ system. For $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, Se selectively occupies the Ch1 sites.

Supplemental Materials

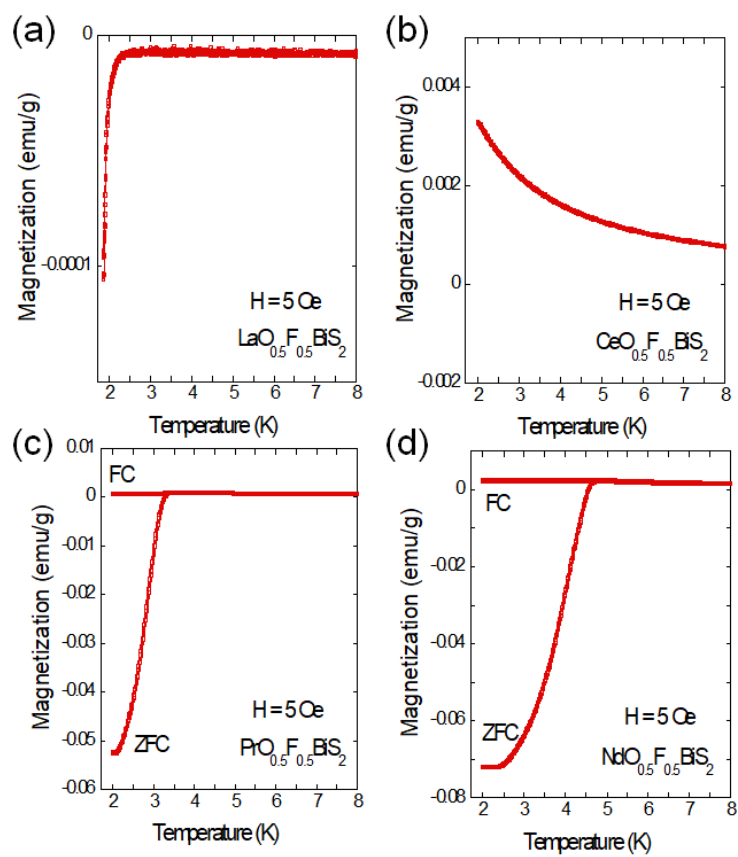


Fig. S1. Temperature dependence of the magnetization for (a) $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, (b) $\text{CeO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, (c) $\text{PrO}_{0.5}\text{F}_{0.5}\text{BiS}_2$, and (d) $\text{NdO}_{0.5}\text{F}_{0.5}\text{BiS}_2$.

Table SI. Crystal structure parameters for $\text{REO}_{0.5}\text{F}_{0.5}\text{BiS}_2$ obtained by the Rietveld refinements. The atomic coordinate for the oxygen (fluorine) site is (0, 0, 0), and the U_{iso} is fixed as 0.013 \AA^2 . The atomic coordinate for other sites is (0, 0.5, z).

RE	La	Ce	Pr	Nd
Space group	<i>P4/nmm</i>	<i>P4/nmm</i>	<i>P4/nmm</i>	<i>P4/nmm</i>
a (\AA)	4.06732(4)	4.03329(2)	4.01708(6)	3.99671(8)
c (\AA)	13.4310(2)	13.48059(10)	13.4008(3)	13.4118(4)
V (\AA^3)	222.189 (4)	219.294(3)	216.247(6)	214.236(8)
R_{wp} (%)	7.7	6.3	6.8	11.6
z (RE)	0.09960(10)	0.09656(7)	0.09822(12)	0.0981(2)
z (Bi)	0.62381(9)	0.62519(7)	0.62468(13)	0.6251(2)
z (S1)	0.3781(6)	0.3789(4)	0.3778(7)	0.3751(11)
z (S2)	0.8119(4)	0.8118(3)	0.8143(6)	0.8160(9)
U_{iso} (RE) (\AA^2)	0.0080(5)	0.0097(4)	0.0084(7)	0.0109(10)
U_{11} (Bi) (\AA^2)	0.0096(4)	0.0093(3)	0.0102(6)	0.0148(9)
U_{33} (Bi) (\AA^2)	0.0265(11)	0.0211(7)	0.0254(14)	0.022(2)
U_{11} (S1) (\AA^2)	0.032(3)	0.021(2)	0.017(3)	0.008(4)
U_{33} (S1) (\AA^2)	0.037(6)	0.027(4)	0.036(7)	0.060(10)
U_{iso} (S2) (\AA^2)	0.007(2)	0.0071(12)	0.005(2)	0.011(4)